

Features

- AEC-Q101 Qualified
- Split Gate Trench MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R_{DS(ON)}
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- · Moisture Sensitivity Level 1

Maximum Ratings

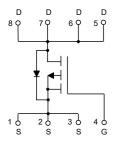
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 20°C/W Junction to Ambient(t≤10s)⁽²⁾
- Thermal Resistance: 50°C/W Junction to Ambient(Steady-State) (2)
- Thermal Resistance: 1.8°C/W Junction to Case(Steady-State)

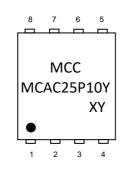
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	-100	V
Gate-Source Volltage	V _{GS}	±20	V
Continuous Drain Current	I _D	-25	Α
Pulsed Drain Current (3)	I _{DM}	-80	Α
Total Power Dissipation ⁽⁴⁾	P _D	70	W
Single Pulsed Avalanche Energy ⁽⁵⁾	E _{AS}	162	mJ

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation PDSM is based on $R_{\theta JA}$ t≤10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. Pd is based on max. junction temperature, using junction-case thermal resistance.
- 5. V_{DD} =50V, V_{G} =-10V, R_{G} =25 Ω , L=1mH.

Internal Structure and Marking Code

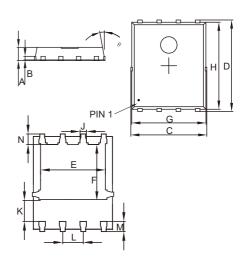




2 codes in total X is the year Y is the month

P-CHANNEL MOSFET

DFN5060



DIMENSIONS						
DIM	INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOIL	
Α	0.031	0.047	0.80	1.20		
В	0.010		0.010 0.254		TYP.	
С	0.193	0.222	4.90	5.64		
D	0.232	0.250	5.90	6.35		
Е	0.148	0.167	3.75	4.25		
F	0.126	0.154	3.20	3.92		
G	0.189	0.213	4.80	5.40		
Н	0.222	0.239	5.65	6.06		
K	0.045	0.059	1.15	1.50		
J	0.012	0.020	0.30	0.50		
L	0.046	0.054	1.17	1.37		
M	0.012	0.028	0.30	0.71		
N	0.016	0.028	0.40	0.71		

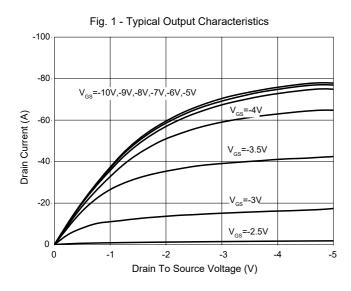


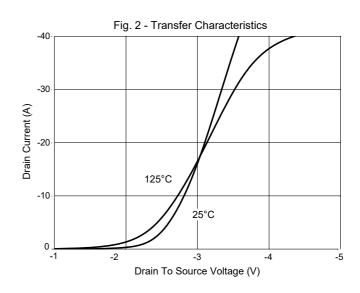
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

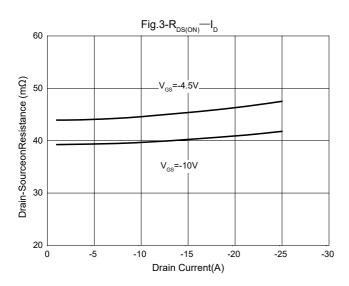
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics			1		1	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-100			V
Gate-Source Leakage Current	I _{GSS}	V_{DS} =0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V			-1	μA
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1	-1.7	-2.5	V
	В	V _{GS} =-10V, I _D =-20A		42	55	mΩ
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-10A		45	60	mΩ
Diode Characteristics	-					
Continuous Body Diode Current	Is				-25	Α
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-10A		-0.9	-1.2	V
Reverse Recovery Time	t _{rr}	1 40 54 11/11 4004/		100		ns
Reverse Recovery Charge	Q _{rr}	I _S =-12.5A,di/dt=100A/μs		280		nC
Dynamic Characteristics	-		,			
Input Capacitance	C _{iss}			2200		
Output Capacitance	C _{oss}	V_{DS} =-50V, V_{GS} =0V,f=1MHz		220		pF
Reverse Transfer Capacitance	C _{rss}			20		
Total Gate Charge	Q_g			40		
Gate-Source Charge	Q _{gs}	V _{DS} =-50V,V _{GS} =-10V,I _D =-12.5A		8		nC
Gate-Drain Charge	Q_{gd}			9		
Turn-On Delay Time	t _{d(on)}			15		
Turn-On Rise Time	t _r	V _{DS} =-50V, I _D =-12.5A		40		no
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V, R_G =6 Ω		105		ns
Turn-Off Fall Time	t _f			110		

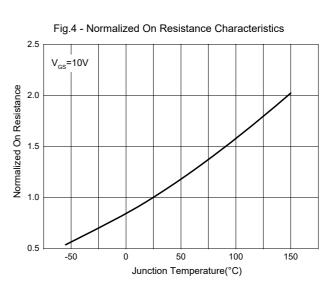


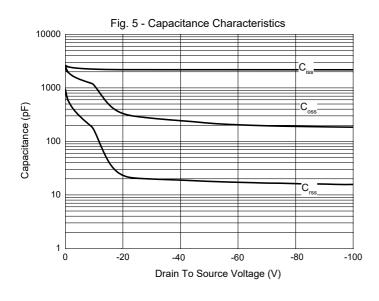
Curve Characteristics

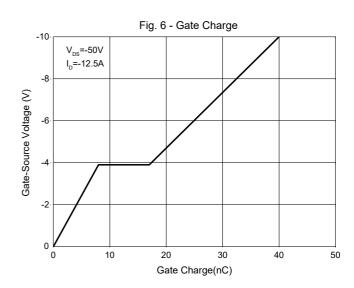














Curve Characteristics

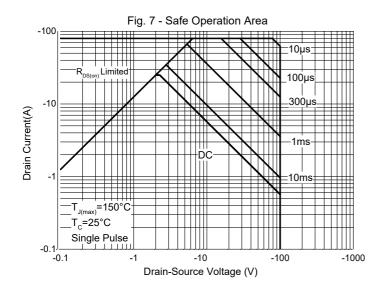
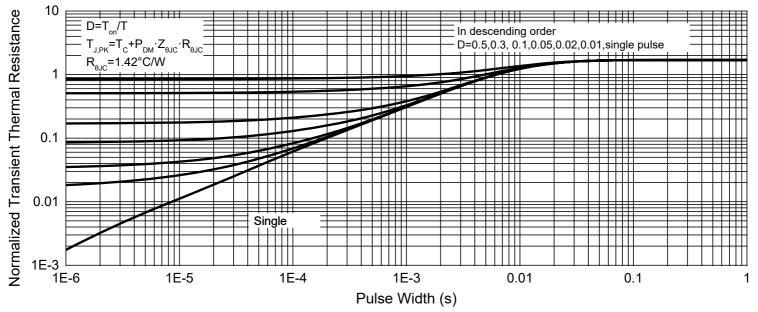


Fig. 8 - Normalized Transient Thermal Impedance



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Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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